

Polarimetry of Light scattered by Surface Roughness and Periodic Structures in Nanotechnologies: A new Challenge in instrumentation and Modeling.

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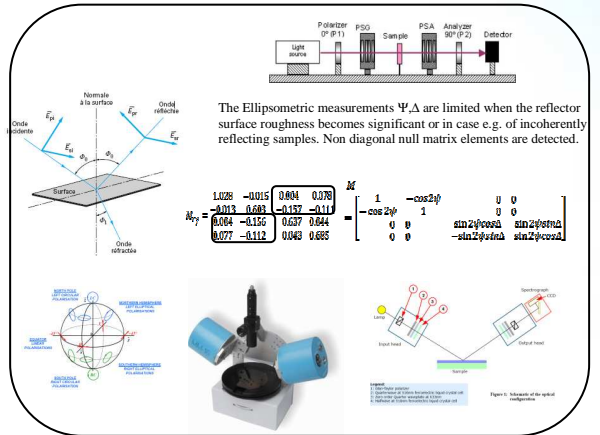
Abstract:

In the literature exhaustive studies detail the Mueller matrices properties through decomposition models, optical entropy and depolarization formalism. Mathematical basis for depolarizing systems, have been first applied in radar polarimetry. In the visible range optics, di-attenuation and retardance decomposition, are present tools today in turbid media analysis. The optical entropy concept provides a very powerful analysis technique yielding important surface parameters such as depolarization, correlation and roughness.

Complementary applications exist in scatterometry, for thin grating films. With high capability polarimeters, the next generation of the angle resolved polarimeters instruments opens new fields of investigation for nanotechnologies materials, lithography applications such as gratings and sophisticated photonics structures.

The theories for surface spectral power density (PSD) and the RCWA theories in periodic structures turn then in a major interest particularly with the recent the S matrix algorithms developments. Behind this instrumentation progress, simulation remains definitely a key point to overcome and will be a challenge between the instruments.

Attempt has been made here to describe the implementation of some of these available codes in applications for surface analysis and with the lithography, (grating overlay) structures.



The Polarimetric Surface scattering model.

Case of a random media and the Stochastics hypothesis.

For a stochastics system with a mean measured Mueller matrix $\langle M \rangle$ turns written as $\langle M \rangle$. Similarly, the model is built over the eigen values of the coherency $\langle T \rangle$. For a stochastics system, each eigen vector, is representing one of the possible states associated to the normalized eigen values, and with the probabilities P_i of the system to be found in this state. The randomness of the system is then characterized, defining the Neumann entropy E , within the interval [0,1].

$$E = - \sum_{i=1}^N p_i \log_N p_i \quad p_i = \lambda_i / \sum_j \lambda_j$$

Within the Bernoulli model, one has an evaluation of a parameter α taking the average of the form

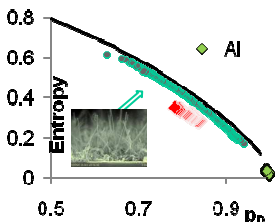
$$\bar{\alpha} = \sum_{i=1}^N P_i \alpha_i \quad (7)$$

Within the special case of diagonal matrices, for an isotropic depolarizer, the Mueller matrix is diagonal. The corresponding coherency $\langle H \rangle$ is also diagonal: In the $[S-Entropy, \alpha]$ space, it will turn to

$$\langle H \rangle = \begin{bmatrix} 1 & 0 & 0 & 0 \\ 0 & m & 0 & 0 \\ 0 & 0 & m & 0 \\ 0 & 0 & 0 & m \end{bmatrix} \quad S = \frac{1}{1+3m} \left\{ \log_2 \frac{m+2m^2}{(1+3m)^{2m-1}} \right\} \quad (9)$$

$$depol = [M]_{00} - \frac{1}{3} \sqrt{([M]_{11})^2 + ([M]_{22})^2 + ([M]_{33})^2} \rightarrow m = \lambda_1 = \lambda_2 = \lambda_3 = \frac{d}{2}$$

$$p_D = \frac{1}{3} \sqrt{\frac{3}{d} (p_D^2 - 1)} = 1 - depol \quad (11) \quad S = -(3p_D + 1)/4 \log_2 \left(\frac{3p_D + 1}{4} \right) - \frac{3(1-p_D)}{4 \log_2 \left(\frac{1-p_D}{4} \right)} \quad (14)$$



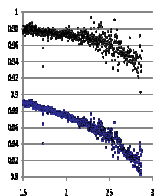
An alternative way to introduce surface disturbance roughness is by a reflection symmetric depolarizing rotation of the Bragg coherency matrix about an angle in a plane perpendicular to the scattering plane. A configurationally averaging has to be taken over a unit surface slopes distribution, S.R. Cloude¹⁰ proposed a slopes distribution uniform of half width with when $b < b_0$, and zero T] appears as:

$$\langle T \rangle = \int_0^{2\pi} [T(\beta)] P(\beta) d\beta \quad (15)$$

$$P(\beta) = \begin{cases} \frac{1}{2} \frac{b_0 - \beta}{b_0} & 0 \leq \beta \leq b_0 \\ 0 & \text{otherwise} \end{cases}$$

$$T = \begin{bmatrix} \cos(2\beta) & 0 & 0 & 0 \\ 0 & \cos(2\beta) & 0 & 0 \\ 0 & 0 & \sin(2\beta) & 0 \\ 0 & 0 & 0 & \sin(2\beta) \end{bmatrix}$$

$$\gamma_{(HH+VV)/(HH-VV)} = \frac{\gamma_{22}}{\sqrt{\gamma_{11} \gamma_{33}}} = \sin(2\beta_0) / \sqrt{1 + \sin^2(\beta_0)} \ll 1.$$



Within this model the polarimetric coherency $\gamma_{(HH+VV)/(HH-VV)}$ is only related to the surface roughness and not of the dielectric properties of the considered material. It can be verified in some cases, e.g., in the case of a 70° incidence measurement on both sides of a Silicon wafer (polished side with native oxide and rough backside of the wafer).

The Mueller matrix Decomposition: How to present experimental Data ?

We adopted the classical representation of the state of polarized light, through the Poincaré sphere. Sample are studied such as one desire to know, the specific behaviour of the surface reflecting sample, or effect of the transmitted light coming from the samples. The Mueller matrix M will give this information through the analysis comparing the Stokes vectors of the light S, S' respectively before and after interaction with the sample $S = M S'$ defined such as

$$S = S_0 [1, \cos 2\epsilon \cos 2\psi, \cos 2\epsilon \sin 2\psi, \sin 2\epsilon]^T$$

$$M = \begin{bmatrix} 1/3 & 0 & 0 & 0 \\ 0 & 1/4 & 0 & 0 \\ 0 & 0 & 1/4 & 0 \\ 0 & 0 & 0 & 1/4 \end{bmatrix}$$

$$M_{r,f} = \begin{bmatrix} 1.028 & -0.015 & 0.004 & 0.078 \\ -0.013 & 0.681 & -0.187 & -0.111 \\ 0.004 & -0.155 & 0.637 & 0.044 \\ 0.077 & -0.112 & 0.043 & 0.695 \end{bmatrix}$$

Normalized and $P < 1$ (the dimmed sphere) and Physically realizable Mueller matrix

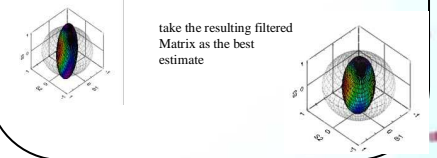
Homomorphism $S[U4 \rightarrow O6]$ enable to relate the Mueller matrix to the coherence matrix. (S.R.Cloude, E.Pottier)

$$[M] = \begin{bmatrix} A_0 + E_0 & C + N & H + I & I + F \\ C - N & A + B & E - J & K + G \\ H - I & E - J & A - B & M + D \\ I - F & K - G & M - D & A_0 - B_0 \end{bmatrix} = [h_j]$$

$$H \equiv T \quad \begin{bmatrix} A_0 + A & C - ID & H + IG & I - J \\ C + ID & B_0 + B & E + JF & K - IL \\ H - IG & E - JF & B_0 - B & M + IN \\ I + IJ & K + IL & M - IN & A_0 - A \end{bmatrix}$$

$T = H = T^T$ is fullfilled

- Matrix Filtering
 - Analysis of the experimental data following the coherence matrix
- $$H \equiv [T_1] = \lambda_0 [T_{00}] + \lambda_1 [T_{11}] + \lambda_2 [T_{22}] + \lambda_3 [T_{33}] +$$
- Example : If λ_1 turns to be a negative value:



s. Y. Lu, R. A. Chipman "Interpretation of Mueller matrices based on polar decomposition" J. of Opt. A,13,1106 (1996).
S.R. Cloude, E. Pottier, "Concept of polarization Entropy in optical scattering" Opt.Eng.,34,6,1599-1610(1995).
Ben Hatit, M. Foldyna, A. de Martino, and B. Drevillon « Angle resolved Mueller Polarimeter using microscope objective » phys. stat. sol. (a) 205, No. 4 (2008)
"ANR-PNano2008 MUELLER FOURIER" LPICM, JYH and LETI 2009-2011 research program for overlay metrology.
See e.g., <http://physics.nist.gov/Divisions/Div844/facilities/scattech/html/>, "Scattech C++ Library" Th., Germer., National Institute of Standard and Technology (NIST),USA

Spectroscopic polarimetry of light scattered by surface roughness and textured films in nanotechnologies. F.Ferrieu published in FCMN09 Albany mars 2009 conference book.



www.leti.fr



1-D structures

NIST SCATMECH C++ Library

Scattero Mueller : One Incidence angle
 Spectroscopic wide band large spot size

$$M = \begin{bmatrix} m_{00} & m_{01} & m_{02} & m_{03} \\ m_{10} & m_{11} & m_{12} & m_{13} \\ m_{20} & m_{21} & m_{22} & m_{23} \\ m_{30} & m_{31} & m_{32} & m_{33} \end{bmatrix}$$

Other S matrix Matlab code

Mueller Fourier Multi Angle
 Narrow band small spot size

NIST SCATMECH C++ Library script files used in optimisation software at LETI

```

BOUNDARIES
v1 v2 oxide medium_1
v3 v4 poly oxide
v4 v5 nitride oxide
v5 v6 nitride poly
v6 v7 nitride poly
v7 v4 nitride poly
v8 v9 medium_1 nitride
v9 v10 resist nitride
v10 v11 medium_1 nitride
v9 v12 medium_1 resist
v12 v10 medium_1 resist
END

WORKING
x1 -period/2
x2 period/2
x3 x1
x4 -period/2+CDs
x5 x2
x6 x3
x7 x4
x8 x5
x9 -period/2+ovl
x10 -period/2+ovl+CDs
x11 x5
x12 x9
x13 x10
x14 0
x15 0
x16 0
x17 0
x18 h
x19 h
x20 h
x21 h
x22 h
x23 h
x24 h
x25 h
x26 h
x27 h
x28 h
x29 h
x30 h
x31 h
x32 0
x33 0
x34 0
x35 0
x36 hs
x37 hs
x38 h-hr
x39 h
x40 h
x41 h
x42 h
x43 h
x44 h
x45 h
x46 h
x47 h
x48 h
x49 h
x50 h
x51 h
x52 h
x53 h
x54 h
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x88 h
x89 h
x90 h
x91 h
x92 h
x93 h
x94 h
x95 h
x96 h
x97 h
x98 h
x99 h
x100 h
END
    
```

CD SEM and AFM 3D

The case of an litho overlay

PARAMETERS ; 2xpat computer FF 2009

```

hs ; The height of the stacked si gratings
hr ; hr
t ; The thickness of the oxide
CDs ; The critical dimension of the resist or Si grating
CDr ; PARAMETERS ; overlay computer FF 2009
hs ; The height of the stacked si gratings
hr ; hr
t ; The thickness of the oxide
CDs ; The critical dimension of the resist or Si grating
CDr ;
shift ; 2x patterns shift
END ; 6 parametres hs hr t CDs CDr ovl
    
```

Matlab Software

Si Substrate

2-D structures

Pillar 2-D

checkboard

Kla description

Nist Script

TEM picture

3-D structures

MUELLER Fourier Project
 LPICM JYH LETI- ANR08 NANO-020-01

86.5 SiO₂ on Si sample experimental data
 Courtesy of LPICM A. De Martino and Ben Hatit et al.: phys. stat. sol. (a) 205, No. 4 (2008)

Examples

Si Grating on Si substrate

Matlab Software

3-D structures